Attorney's Docket No.: 07977-004002 / US2931/2949D1

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Naoto Kusumoto et al.
Serial No. : 10/602,762
Filed : June 25, 2003
Title : LASER ANNEALING METHOD

Art Unit : 2828
Examiner : Delma Flores Ruiz

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

SUBMISSION OF CORRECTED FORM PTO-1449

Supplemental to an information disclosure statement filed with the application on June 25, 2003, applicants submit the attached corrected Form PTO-1449. All of the documents listed on the form PTO-1449 were cited in the information disclosure statement filed with the application. The corrected Form PTO-1449 is being submitted to correctly recite the country for reference "AU" as "South Africa" instead of "China."

No fees are believed to be due. Please apply any charges or credits to Deposit Account No. 06-1050.

Respectfully submitted,

Date: 3/28/05

John F. Hayden
Reg. No. 37,640

Fish & Richardson P.C.
1425 K Street, N.W.
11th Floor
Washington, DC 20005-3500
Telephone: (202) 783-5070
Facsimile: (202) 783-2331

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Substitute Form PTO-1449 (Modified)	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. 07977-004002	Application No. 10/602,762
Corrected Information Disclosure Statement by Applicant (Use several sheets if necessary) (37 CFR §1.98(b))		Applicant Naoto Kusumoto et al.	
		Filing Date June 25, 2003	Group Art Unit 2828

U.S. Patent Documents

Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
	AA	3,585,088	06/1971	Scwuttke et al.			
	AB	4,195,913	4/1/80	Dourte et al.			
	AC	4,475,027	10/2/84	Pressley			
	AD	5,145,808	09/1995	Sameshima et al.			
	AE	5,219,786	6/15/93	Noguchi			
	AF	5,304,357	04/1994	Sato et al.			
	AG	5,365,875	11/1994	Asai et al.			
	AH	5,424,244	6/13/95	Zhang, et al.			
	AI	5,432,122	07/1995	Chae			
	AJ	5,477,073	12/1995	Wakai et al.			
	AK	5,496,768	03/1996	Kudo			
	AL	5,561,081	02/1994	Takenouchi et al.			
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	AN	5,643,801	7/1/97	Ishihara, et al.			
	AO	5,795,795	8/18/98	Kousai, et al.			
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	AR	5,897,799	4/27/99	Yamazaki et al			
	AS	6,143,661	11/7/2000	Kousai, et al.			
	AT	6,358,784	03/19/2002	Zhang, et al			

Foreign Patent Documents or Published Foreign Patent Applications

Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation Yes	Translation No
	AU	ZA8306334	03/1984	**South Africa**				
	AV	64-76715	03/1989	Japan				
	AW	1-76715	03/1989	Japan				
	AX	3-286518	12/1991	Japan				

Examiner Signature	Date Considered
EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

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Foreign Patent Documents or Published Foreign Patent Applications

Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation Yes	Translation No
	AY	4-307727	10/1992	Japan				

Other Documents (include Author, Title, Date, and Place of Publication)

Examiner Initial	Desig. ID	Document
	AZ	Anderson et al.; "Characterization of the substrate interface of excimer laser crystallized polysi..."; *MRS Symp. Proc. 343*; pp. 709; 1994
	AAA	Brotherton et al.; "Beam shape effects with EL crystallization of...a-Si"; *Solid State Phenomena 37-38*; pp. 299-304; 1994
	ABB	Carluccio et al., "Microstructure of Polycrystalline Silicon Films Obtained by Combined Furnace and Laser Annealing", Appl. Phys. Lett., Vol. 66, No. 11, pp. 1394-1396
	ACC	Caune et al.; "Combined CW laser and furnace annealing of a-Si and Ge in contact with some metals"; *Appl. Surf. Sci. 36*; p. 597; 1989
	ADD	Hayashi et al.; "Fabrication of Low-Temperature Bottom-Gate Poly-Si TFTs on Large-Area Substrate by Linear-Beam Excimer Laser Crystallization and Ion Doping Method"; *IEEE IEDM*; pp. 829-832; 1995
	AEE	Jhon et al.; "Crystallization of Amorphous Silicon by Excimer Laser Annealing with a Line Shape Beam Having a Gaussian Profile"; *Japan Journal of Applied Physics, Vol. 33*; pp. 1438-1441; October 1994
	AFF	Jhon et al.; "Crystallization of a-Si by ELA with a line shape beam having a Gaussian profile"; *Jpn. J. Appl. Phys 33(10B)*; p. L1438; October 1994
	AGG	Kohno et al., "High Performance Poly-Si TFTs Fabricated Using Pulsed Laser Annealing and Remote Plasma CVD with Low Temperature Processing", IEEE Transactions on Electron Devices, Vol. 42, No. 2, pp. 251-257
	AHH	Kuriyama et al.; "Improving...ELA method for giant microelectronics"; *Jpn. J. Appl. Phys. 31(12B)*; p. 4550; December 1992
	AII	Kuriyama et al.; "Lateral growth of Poly-Si films...by ELA..."; *Jpn. J. Appl. Phys. 32(12B)*; p. 6190; December 1993
	AJJ	Okumura et al.; "Excimer laser annealed poly-Si TFT technologies"; *MRS Symp. Proc. 377*; p. 877; April 1995
	AKK	Sweatt; "Transforming a circular laser beam into a square or trapezoid..."; *Optical Eng. 31(2)*; p. 245; February 1992

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